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November 2013

FQB11P06

P-Channel QFET® MOSFET

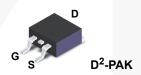
-60 V, -11.4 A, 175 mΩ

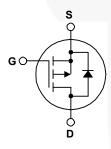
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- -11.4 A, -60 V, $R_{DS(on)}$ = 175 m Ω (Max.) @ V_{GS} = -10 V, I_D = -5.7 A
- Low Gate Charge (Typ. 13 nC)
- Low Crss (Typ. 45 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQB11P06TM	Unit
V _{DSS}	Drain-Source Voltage		-60	V
I _D	Drain Current - Continuous (T _C = 25°C)		-11.4	Α
	- Continuous (T _C = 100°C)		-8.05	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	-45.6	Α
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		160	mJ
I _{AR}	Avalanche Current	(Note 1)	-11.4	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	5.3	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		-7.0	V/ns
P _D	Power Dissipation (T _A = 25°C) *		3.13	W
	Power Dissipation (T _C = 25°C)		53	W
	- Derate above 25°C		0.35	W/°C
T_J , T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T _L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQB11P06TM	Unit
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max.	2.85	
В	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQB11P06TM	FQB11P06	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Uni
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-60			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, Referenced to 25°	C	-0.07		V/°(
I _{DSS}	Zana Cata Valtana Duain Cumunt	V _{DS} = -60 V, V _{GS} = 0 V			-1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = -48 V, T _C = 150°C			-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-2.0		-4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -5.7 A		0.14	0.175	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = -30 \text{ V}, I_{D} = -5.7 \text{ A}$		5.1		S
Dynam C _{iss}	ic Characteristics Input Capacitance			420	550	n.E
Coss	Output Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$		195	250	pF pF
C _{rss}	Reverse Transfer Capacitance	f = 1.0 MHz		45	60	рF
rss	reverse transfer capacitance			43	00	рі
Switch	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = -30 V, I _D = -5.7 A,		6.5	25	ns
t _r	Turn-On Rise Time	$R_{G} = 25 \Omega$		40	90	ns
t _{d(off)}	Turn-Off Delay Time	11.6 20 22		15	40	ns
t _f	Turn-Off Fall Time	(Note	4)	45	100	ns
Qg	Total Gate Charge	V _{DS} = -48 V, I _D = -11.4 A,		13	17	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V		2.0		nC
Q _{gd}	Gate-Drain Charge	(Note	4)	6.3		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				-11.4	Α
	Maximum Pulsed Drain-Source Diode F	Forward Current			-45.6	Α
I_{SM}						
	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -11.4 \text{ A}$			-4.0	V
V_{SD}	Drain-Source Diode Forward Voltage Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_S = -11.4 \text{ A}$ $V_{GS} = 0 \text{ V, } I_S = -11.4 \text{ A,}$		83	-4.0 	V ns

- Notes:
 1. Repetitive rating : pulse-width limited by maximum junction temperature.
 2. L = 1.44 mH, I_{AS} = -11.4 A, V_{DD} = -25 V, R_G = 25 Ω , starting T_J = 25°C.
 3. I_{SD} ≤ -11.4 A, di/dt ≤ 300 A/µs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C .
 4. Essentially independent of operating temperature

Typical Characteristics

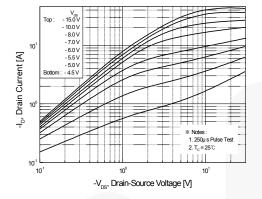


Figure 1. On-Region Characteristics

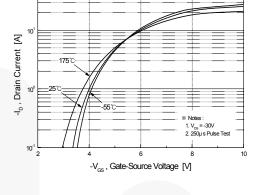


Figure 2. Transfer Characteristics

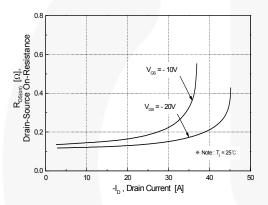


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

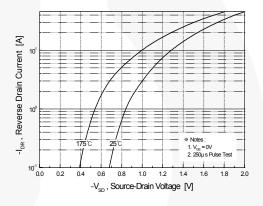


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

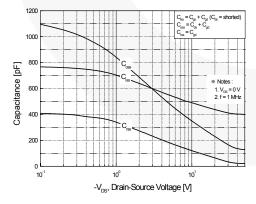


Figure 5. Capacitance Characteristics

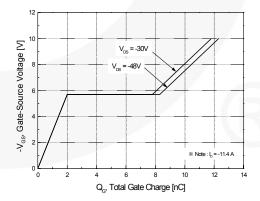


Figure 6. Gate Charge Characteristics

Drain-Source Breakdown Voltage 10 *Notes:: 1.V^{cs} = 0.0 2 l^c = -50 h y

-100

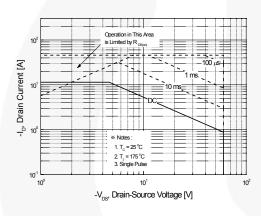
Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

T_., Junction Temperature [°C]

150

Figure 8. On-Resistance Variation vs. Temperature



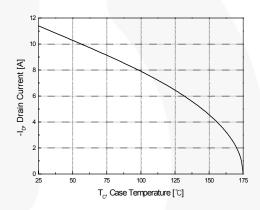


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

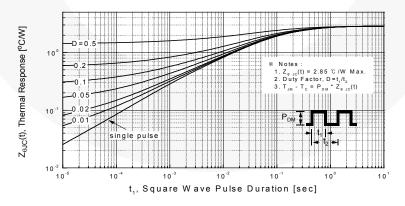


Figure 11. Transient Thermal Response Curve

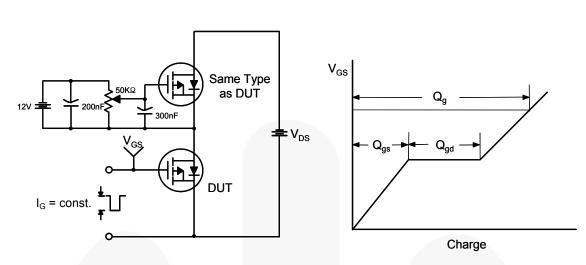


Figure 12. Gate Charge Test Circuit & Waveform

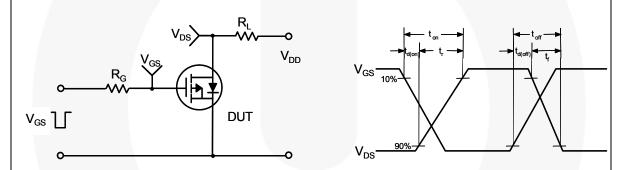


Figure 13. Resistive Switching Test Circuit & Waveforms

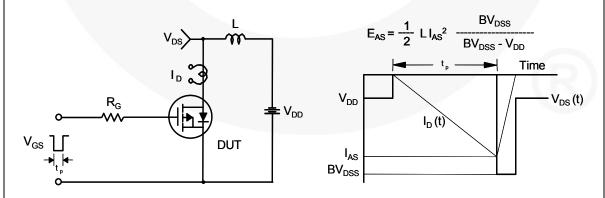
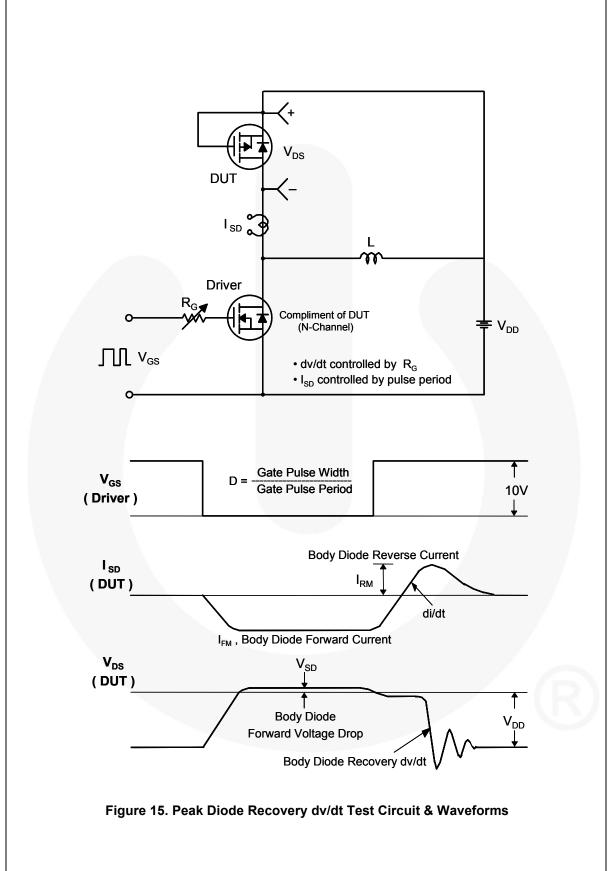


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

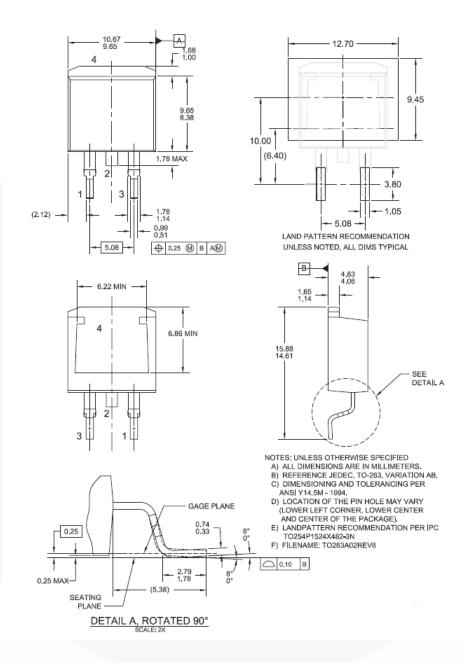


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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